

Abstracts

A New Empirical Nonlinear Model for HEMT-Devices

I. Angelov, H. Zirath and N. Rorsman. "A New Empirical Nonlinear Model for HEMT-Devices." 1992 MTT-S International Microwave Symposium Digest 92.3 (1992 Vol. III [MWSYM]): 1583-1586.

A new large signal model for HEMTs, capable of modeling the current-voltage characteristic, and its derivatives, including the characteristic transconductance peak, gate-source- and gate-drain- capacitances is described. Model parameter extraction is straightforward and is made for a submicron gatelength /spl part/-doped pseudomorphic HEMT. Measured and modeled DC- and S-parameters are compared.

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